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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/560,573	12/12/2005	Theodore Letavic	US03 0162 US2	6633
65913 NXP , B.V.	7590 03/20/200	EXAMINER		
NXP INTELLECTUAL PROPERTY DEPARTMENT			KEBEDE, BROOK	
	M/S41-SJ 1109 MCKAY DRIVE			PAPER NUMBER
SAN JOSE, CA 95131			2823	
			NOTIFICATION DATE	DELIVERY MODE
			03/20/2008	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
	10/560,573	LETAVIC, THEODORE	
Office Action Summary	Examiner	Art Unit	
	Brook Kebede	2823	
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING D - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tin will apply and will expire SIX (6) MONTHS from e, cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).	
Status			
1) ☐ Responsive to communication(s) filed on 31 Jac 2a) ☐ This action is FINAL . 2b) ☐ This 3) ☐ Since this application is in condition for allowated closed in accordance with the practice under Bacterian.	s action is non-final. nce except for formal matters, pro		
Disposition of Claims			
4) Claim(s) 1-3 and 12-19 is/are pending in the a 4a) Of the above claim(s) 15-19 is/are withdray 5) Claim(s) is/are allowed. 6) Claim(s) 1-3 and 12-14 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/o	wn from consideration.		
Application Papers			
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) accomposed and all accomposed and all accomposed and accomposed accomposed and accomposed and accomposed and accomposed and accomposed and accomposed and accomposed accomposed accomposed and accomposed accomposed accomposed accomposed accomposed accomposed accomposed accomposed accomposed and accomposed	cepted or b) objected to by the liderawing(s) be held in abeyance. See tion is required if the drawing(s) is objected.	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Burea * See the attached detailed Office action for a list	ts have been received. ts have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National Stage	
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal F 6) Other:	ate	

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DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on January 31, 2008 has been entered.

Election/Restrictions

2. Newly submitted claims 15-19 are directed to an invention that is independent or distinct from the invention originally claimed for the following reasons:

The subject matter of the newly added claims, i.e., claims 15-19, is similar to that of previously withdrawn claims, i.e., 4-9 due to response of the restriction requirement of February 14, 2007.

Since applicant has received an action on the merits for the originally presented invention, this invention has been constructively elected by original presentation for prosecution on the merits. Accordingly, claims 15-19 are withdrawn from consideration as being directed to a non-elected invention. See 37 CFR 1.142(b) and MPEP § 821.03.

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

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4. Claims 1-3 and 12-19 are rejected under 35 U.S.C. 102(b) as being anticipated by Mitsubishi et al. (US 6,545,318).

Re claim 1, Mitsubishi et al. disclose a thin film Silicon on Insulator (SOI) device comprising: a source (72 74); a gate (6); a drain (82 84); an SOI layer (3); a substrate layer (1), wherein when the substrate layer (1) is maintained at a potential sufficiently lower than a potential of the source a parasitic MOS channel is formed between the source and drain; and a Deep N implant layer (73 83) formed between either the source (72) or drain (82) and the SOI (3) layer to prevent flow of current between the source and drain via the parasitic MOS channel when the device is in an off state (see Figs. 1-24 and related text in Col. 2, line 35 - Col. 23, line 11).

Re claim 2, as applied to claim 1 above, Mitsubishi et al. disclose all the claimed limitation including wherein the Deep N implant layer is formed between the source and the SOI layer (see Figs. 1-24 and related text in Col. 2, line 35 - Col. 23, line 11).

Re claim 3, as applied to claim 1 above, Mitsubishi et al. disclose all the claimed limitation including wherein the Deep N implant layer is formed between the drain and the SOI insulator layer (see Figs. 1-24 and related text in Col. 2, line 35 - Col. 23, line 11).

Claim Rejections - 35 USC § 103

5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

⁽a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

6. Claims 12-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mitsubishi et al. (US 6,545,318)

Re claim 12, as applied to claim 1 in Paragraph 3 above, Mitsubishi et al. discloses all the claimed limitations including maintaining the source potential greater than the substrate potential (i.e., it is standard PMOS transistor operation that PN junction is biased in a forward direction, the threshold voltage is lowered, and the operation is accelerated when the substrate potential is lower than the source potential).

Furthermore, the claimed voltage can be routinely adjusted by routine optimization in order to efficiently operate the device.

One of ordinary skill in the art would have been motivated to optimize the claimed voltage range by using routine experimentation in order to efficiently operate the device.

Therefore, it would have been to one having ordinary skill in the art at the time of the invention is made to optimize the claimed voltage range, since it has been held where the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." See *In re Aller*, 220 F.2d 454, 456, 105 USPQ 233, 235 (CCPA 1955); *In re Hoeschele*, 406 F.2d 1403, 160 USPQ 809 (CCPA 1969); *Merck & Co. Inc. v. Biocraft Laboratories Inc.*, 874 F.2d 804, 10 USPQ2d 1843 (Fed. Cir.), cert. denied, 493 U.S. 975 (1989); *In re Kulling*, 897 F.2d 1147, 14 USPQ2d 1056 (Fed. Cir. 1990); and *In re Geisler*, 116 F.3d 1465, 43 USPQ2d 1362 (Fed. Cir. 1997). Furthermore, the specification contains no disclosure of either the critical nature of the claimed voltage value or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimensions or upon another variable recited in a claim, the Applicant must show that the

chosen dimensions are critical. See *In re Woodruff*, 919, f.2d 1575, 1578, 16 USPQ2d, 1936 (Fed. Cir. 1990).

Re claim 13, as applied to claim 1 in Paragraph 3 above, Mitsubishi et al. disclose all the claimed limitations including the SOI layer having predetermined thickness.

Furthermore the claimed thickness range can be achieved by routine optimization in order to achieve the desired device performance and size.

Notwithstanding, one of ordinary skill in the art would have been led to the recited dimensions through routine experimentation and optimization. Applicant has not disclosed that the dimensions are for a particular unobvious purpose, produce an unexpected result, or are otherwise critical, and it appears prima facie that the process would possess utility using another dimension. Indeed, it has been held that mere dimensional limitations are prima facie obvious absent a disclosure that the limitations are for a particular unobvious purpose, produce an unexpected result, or are otherwise critical. See, for example, *In re Rose*, 220 F.2d 459, 105 USPQ 237 (CCPA 1955); *In re Rinehart*, 531 F.2d 1048, 189 USPQ 143 (CCPA 1976); *Gardner v. TEC Systems, Inc.*, 725 F.2d 1338, 220 USPQ 777 (Fed. Cir. 1984), cert. denied, 469 U.S. 830, 225 USPQ 232 (1984); *In re Dailey*, 357 F.2d 669, 149 USPQ 47 (CCPA 1966).

Re claim 14, applied to claim 1 in Paragraph 3 above, Mitsubishi et al. disclose all the claimed limitations including wherein the Deep N implant layer has a doping concentration about predetermined order of magnitude higher than that of a gate region associated with the gate.

Furthermore, the claimed concentration can be set by routine optimization in order to a achieve the desired implant depth and impurity level.

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Therefore, it would have been to one having ordinary skill in the art at the time of the invention is made to optimize the claimed implant concentration range, since it has been held where the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." See *In re Aller*, 220 F.2d 454, 456, 105 USPQ 233, 235 (CCPA 1955); *In re Hoeschele*, 406 F.2d 1403, 160 USPQ 809 (CCPA 1969); *Merck & Co. Inc. v. Biocraft Laboratories Inc.*, 874 F.2d 804, 10 USPQ2d 1843 (Fed. Cir.), cert. denied, 493 U.S. 975 (1989); *In re Kulling*, 897 F.2d 1147, 14 USPQ2d 1056 (Fed. Cir. 1990); and *In re Geisler*, 116 F.3d 1465, 43 USPQ2d 1362 (Fed. Cir. 1997). Furthermore, the specification contains no disclosure of either the critical nature of the claimed concentration range or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimensions or upon another variable recited in a claim, the Applicant must show that the chosen dimensions are critical. See *In re Woodruff*, 919, f.2d 1575, 1578, 16 USPQ2d, 1936 (Fed. Cir. 1990).

Response to Arguments

7. Applicant's arguments with respect to claims 1-3 and 12-14 have been considered but are moot in view of the new ground(s) of rejection necessitated by the amendment filed on December 26, 2007.

Conclusion

8. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure Hwang (US 5,259,219) also disclose similar inventive subject matter.

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Correspondence

9. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Brook Kebede whose telephone number is (571) 272-1862. The

examiner can normally be reached on 8-5 Monday to Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Matthew S. Smith can be reached on (571) 272-1907. The fax phone number for the

organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent

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information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Brook Kebede/

Primary Examiner, Art Unit 2823

/BK/

March 12, 2008